

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Canceled)

2. (Currently Amended) ~~The fabricating method as defined in claim 1, A method for fabricating a mask, comprising:~~

~~forming a film to be patterned;~~

~~forming, on said film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern; and~~

~~increasing a width of said top resist pattern after said film is patterned via said laminated resist pattern,~~

~~wherein said bottom resist pattern is made of polymethylglutarimide (PMGI).~~

3. (Currently Amended) ~~The fabricating method as defined in claim 1, A method for fabricating a mask, comprising:~~

~~forming a film to be patterned;~~

~~forming, on said film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern; and~~

~~increasing a width of said top resist pattern after said film is patterned via said laminated resist pattern,~~

~~wherein said top resist pattern is made of a resist material with phenol-based hydroxide.~~

4. (Currently Amended) ~~The fabricating method as defined in claim 1, A method for fabricating a mask, comprising:~~

forming a film to be patterned;  
forming, on said film, a laminated resist pattern with a T-shaped cross section  
and composed of a bottom resist pattern and a top resist pattern, a surface area of said top  
resist pattern being larger than a surface area of said bottom resist pattern; and  
increasing a width of said top resist pattern after said film is patterned via said  
laminated resist pattern,

wherein said surface area of said top resist pattern is increased by coating a  
water-soluble resin at least over said top resist pattern of said laminated resist pattern.

5. (Original) The fabricating method as defined in claim 4, wherein said water-soluble resin contain no crosslinking agent, and said surface area of said top resist pattern is increased due to the shrinkage of said water-soluble resin.

6. (Original) The fabricating method as defined in claim 4, wherein said water-soluble resin contain a crosslinking agent, and said surface area of said top resist pattern is increased by the formation of a membrane at least over said top resist pattern.

7. (Currently Amended) The fabricating method as defined in claim 1, A method  
for fabricating a mask, comprising:

forming a film to be patterned;  
forming, on said film, a laminated resist pattern with a T-shaped cross section  
and composed of a bottom resist pattern and a top resist pattern, a surface area of said top  
resist pattern being larger than a surface area of said bottom resist pattern; and  
increasing a width of said top resist pattern after said film is patterned via said  
laminated resist pattern,

wherein said laminated resist pattern is not removed through the fabrication  
process of patterned thin film.

8. (Currently Amended) The fabricating method as defined in claim 1, A method for fabricating a mask, comprising:

forming a film to be patterned;

forming, on said film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern; and

increasing a width of said top resist pattern after said film is patterned via said laminated resist pattern,

wherein said film is patterned via said laminated resist pattern by means of dry etching.

9. (Canceled)

10. (Currently Amended) The fabricating method as defined in claim 9, A method for fabricating a patterned thin film, comprising:

forming a first thin film to be patterned;

forming, on said first thin film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern;

patterning said first thin film via said laminated resist pattern, to form a first patterned thin film;

increasing a width of said top resist pattern; and

forming a second patterned thin film along a contour of said top resist pattern of said laminated resist pattern,

wherein said bottom resist pattern is made of polymethylglutarimide (PMGI).

11. (Currently Amended) The fabricating method as defined in claim 9, A method for fabricating a patterned thin film, comprising:

forming a first thin film to be patterned;  
forming, on said first thin film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern;  
patterning said first thin film via said laminated resist pattern, to form a first patterned thin film;  
increasing a width of said top resist pattern; and  
forming a second patterned thin film along a contour of said top resist pattern of said laminated resist pattern,  
wherein said top resist pattern is made of a resist material with phenol-based hydroxide.

12. (Currently Amended) ~~The fabricating method as defined in claim 9, A method for fabricating a patterned thin film, comprising:~~  
forming a first thin film to be patterned;  
forming, on said first thin film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern;  
patterning said first thin film via said laminated resist pattern, to form a first patterned thin film;  
increasing a width of said top resist pattern; and  
forming a second patterned thin film along a contour of said top resist pattern of said laminated resist pattern,  
wherein said surface area of said top resist pattern is increased by coating a water-soluble resin at least over said top resist pattern of said laminated resist pattern.

13. (Original) The fabricating method as defined in claim 12, wherein said water-soluble resin contain no crosslinking agent, and said surface area of said top resist pattern is increased due to the shrinkage of said water-soluble resin.

14. (Original) The fabricating method as defined in claim 12, wherein said water-soluble resin contain a crosslinking agent, and said surface area of said top resist pattern is increased by the formation of a membrane at least over said top resist pattern.

15. (Currently Amended) ~~The fabricating method as defined in claim 9, A method for fabricating a patterned thin film, comprising:~~

forming a first thin film to be patterned;  
forming, on said first thin film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern;  
patterning said first thin film via said laminated resist pattern, to form a first patterned thin film;

increasing a width of said top resist pattern; and  
forming a second patterned thin film along a contour of said top resist pattern of said laminated resist pattern,

wherein said laminated resist pattern is not removed through the fabrication process of said first patterned thin film and said second patterned thin film.

16. (Currently Amended) ~~The fabricating method as defined in claim 9, A method for fabricating a patterned thin film, comprising:~~

forming a first thin film to be patterned;  
forming, on said first thin film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern;

patterning said first thin film via said laminated resist pattern, to form a first patterned thin film;

increasing a width of said top resist pattern; and

forming a second patterned thin film along a contour of said top resist pattern of said laminated resist pattern,

wherein said film is patterned via said laminated resist pattern by means of dry etching.

17. (Currently Amended) The fabricating method as defined in claim 9, A method for fabricating a patterned thin film, comprising:

forming a first thin film to be patterned;

forming, on said first thin film, a laminated resist pattern with a T-shaped cross section and composed of a bottom resist pattern and a top resist pattern, a surface area of said top resist pattern being larger than a surface area of said bottom resist pattern;

patterning said first thin film via said laminated resist pattern, to form a first patterned thin film;

increasing a width of said top resist pattern; and

forming a second patterned thin film along a contour of said top resist pattern of said laminated resist pattern,

wherein said second patterned thin film is located away from said first patterned thin film by a minute gap.

18. (Original) The fabricating method as defined in claim 17, wherein said second patterned thin film is composed of a pair of patterned thin films, which are located at both sides of said first patterned thin film by minute gaps.

19-22. (Canceled)